

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

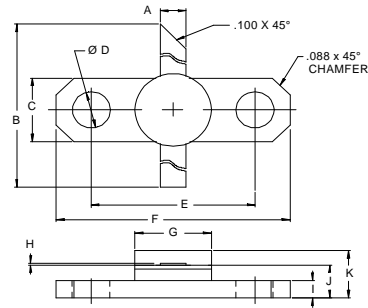
The **ASI AVD004F** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	650 mA PEAK
V_{CB}	32 V
P_{DISS}	18 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.0 °C/W

PACKAGE STYLE .250 2L FLG(B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

ORDER CODE: ASI10554
CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1\text{ mA}$	45			V
BV_{CER}	$I_C = 5\text{ mA}$ $R_{BE} = 10\ \Omega$	45			V
BV_{EBO}	$I_E = 1\text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 28\text{ V}$			1.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 200\text{ mA}$	30		300	---
P_G	$V_{CC} = 28\text{ V}$ $P_{OUT} = 4.0\text{ W}$ $f = 1025 - 1150\text{ MHz}$	9.0			Db
η_C		35			%